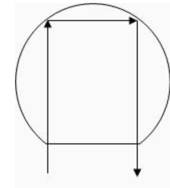
Part Number	Customer

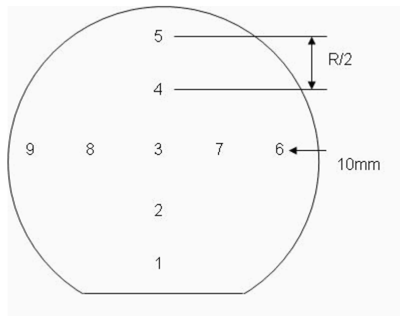
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none/semi standard	
	5.0	Overall Thickness	1,002.00 +/- 7.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00	ADE to ASTM F657
	7.0	Bow	<60.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Fusion bonding alignment error	Between handle and SOI primary flats 0 deg +/- 1deg	Guaranteed by process
	12.0	Front Surface Quality	Polished, roughness <5A	Guaranteed by process
HandleSilicon	13.0	Handle Growth Method	FZ	Wafer Vendor
	14.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	15.0	Handle Thickness	750.00 +/- 5.00 µm	ADE, 100%
	16.0	Handle Doping Type	P	Wafer Vendor
	17.0	Handle Dopant	Boron	Wafer Vendor
	18.0	Handle Resistivity	>1000 Ohmcm	Wafer Vendor
	19.0	Backside Finish	Polished with oxide and lasermarking	Guaranteed by process
BuriedOxide	20.0	Oxide Type	Thermal	
	21.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	22.0	Oxide formed on	Handle Wafer	
DeviceSilicon	23.0	Device Growth Method	FZ	Wafer Vendor
	24.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	25.0	Nominal Thickness	250.00 +/- 1.00 µm	FTIR, 100% 9-Pt (note3)
	26.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	27.0	Device Doping Type	P	Wafer Vendor
	28.0	Device Dopant	Boron	Wafer Vendor
	29.0	Device Resistivity	>1000 Ohmcm	Wafer Vendor
	30.0	Voids	none	Wafer Vendor
	31.0	Scratches	none	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information